

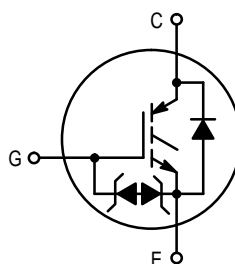
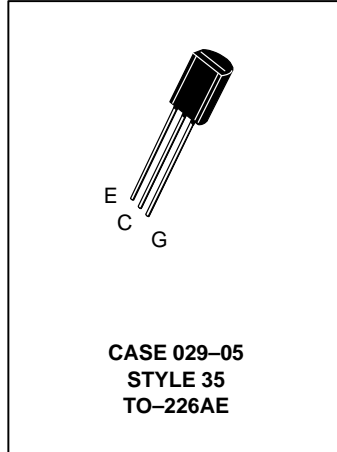
Designer's™ Data Sheet
Insulated Gate Bipolar Transistor
N-Channel Enhancement-Mode Silicon Gate

MGS05N60D

This IGBT contains a built-in free wheeling diode and a gate protection zener diodes. Fast switching characteristics result in efficient operation at higher frequencies. This device is ideally suited for high frequency electronic ballasts.

IGBT
0.5 A @ 25°C
600 V

- Built-In Free Wheeling Diodes
- Built-In Gate Protection Zener Diode
- Industry Standard Package (TO92 — 1.0 Watt)
- High Speed E_{off} : Typical 6.5 μ s @ $I_C = 0.3$ A; $T_C = 125^\circ$ C and $dV/dt = 1000$ V/ μ s
- Robust High Voltage Termination
- Robust Turn-Off SOA



MAXIMUM RATINGS ($T_C = 25^\circ$ C unless otherwise noted)

Parameters	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CES}	600	Vdc
Collector-Gate Voltage ($R_{GE} = 1.0$ M Ω)	V_{CGR}	600	Vdc
Gate-Emitter Voltage — Continuous	V_{GES}	± 15	Vdc
Collector Current — Continuous @ $T_C = 25^\circ$ C — Continuous @ $T_C = 90^\circ$ C — Repetitive Pulsed Current (1)	I_{C25} I_{C90} I_{CM}	0.5 0.3 2.0	Adc
Total Power Dissipation	P_D	1.0	Watt
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ$ C

THERMAL CHARACTERISTICS

Thermal Resistance — Junction to Case – IGBT — Junction to Ambient	$R_{\theta JC}$ $R_{\theta JA}$	25 125	$^\circ$ C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	T_L	260	$^\circ$ C

UNCLAMPED DRAIN-TO-SOURCE AVALANCHE CHARACTERISTICS ($T_C \leq 150^\circ$ C)

Single Pulse Drain-to-Source Avalanche Energy – Starting @ $T_C = 25^\circ$ C @ $T_C = 125^\circ$ C $V_{CE} = 100$ V, $V_{GE} = 15$ V, Peak $I_L = 2.0$ A, $L = 3.0$ mH, $R_G = 25$ Ω	E_{AS}	125 40	mJ
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(1) Pulse width is limited by maximum junction temperature repetitive rating.

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-to-Emitter Breakdown Voltage (V _{GE} = 0 Vdc, I _C = 250 μAdc) Temperature Coefficient (Positive)	V _{(BR)CES}	600 —	680 0.7	— —	Vdc V/°C
Zero Gate Voltage Collector Current (V _{CE} = 600 Vdc, V _{GE} = 0 Vdc) (V _{CE} = 600 Vdc, V _{GE} = 0 Vdc, T _C = 125°C)	I _{CES} I _{CES}	— —	0.1 5.0	5.0 50	μAdc
Gate-Body Leakage Current (V _{GE} = ±15 Vdc, V _{CE} = 0 Vdc)	I _{GES}	—	10	100	μAdc

ON CHARACTERISTICS

Collector-to-Emitter On-State Voltage (V _{GE} = 15 Vdc, I _C = 0.3 Adc) (V _{GE} = 15 Vdc, I _C = 0.3 Adc, T _C = 125°C)	V _{CE(on)}	— —	1.6 1.5	2.0 —	Vdc
Gate Threshold Voltage (V _{CE} = V _{GE} , I _C = 250 μAdc) Threshold Temperature Coefficient (Negative)	V _{GE(th)}	3.5 —	— 6.0	6.0 —	Vdc mV/°C
Forward Transconductance (V _{CE} = 10 Vdc, I _C = 0.5 Adc)	g _{fe}	0.3	0.42	—	Mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	(V _{CE} = 20 Vdc, V _{GE} = 0 Vdc, f = 1.0 MHz)	C _{ies}	—	75	100	pF
Output Capacitance		C _{oes}	—	11	20	
Transfer Capacitance		C _{res}	—	1.6	5.0	

DIODE CHARACTERISTICS

Diode Forward Voltage Drop (I _{EC} = 0.3 Adc) (I _{EC} = 0.3 Adc, T _C = 125°C) (I _{EC} = 0.1 Adc) (I _{EC} = 0.1 Adc, T _C = 125°C)	V _{FEC}	— — — —	5.0 5.2 2.3 2.3	6.0 — 3.0 —	Vdc	
Reverse Recovery Time	(I _F = 0.4 Adc, V _R = 300 Vdc, dI _F /dt = 10 A/μs)	t _{rr}	—	150	—	ns
Reverse Recovery Stored Charge		Q _{RR}	—	35	—	μC

SWITCHING CHARACTERISTICS (1)

Turn-Off Delay Time	(V _{CC} = 300 Vdc, I _C = 0.4 Adc, V _{GE} = 15 Vdc, L = 3.0 mH, R _G = 25 Ω, dV/dt = 1000 V/μs) Energy losses include "tail"	t _{d(off)}	—	28	—	ns
Fall Time		t _f	—	150	—	
Turn-Off Switching Loss		E _{off}	—	3.25	4.25	
Turn-Off Delay Time	(V _{CC} = 300 Vdc, I _C = 0.4 Adc, V _{GE} = 15 Vdc, L = 3.0 mH, R _G = 25 Ω, T _C = 125°C, dV/dt = 1000 V/μs) Energy losses include "tail"	t _{d(off)}	—	21	—	ns
Fall Time		t _f	—	280	—	
Turn-Off Switching Loss		E _{off}	—	8.0	10	
Gate Charge	(V _{CC} = 300 Vdc, I _C = 0.3 Adc, V _{GE} = 15 Vdc)	Q _T	—	6.4	—	nC

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

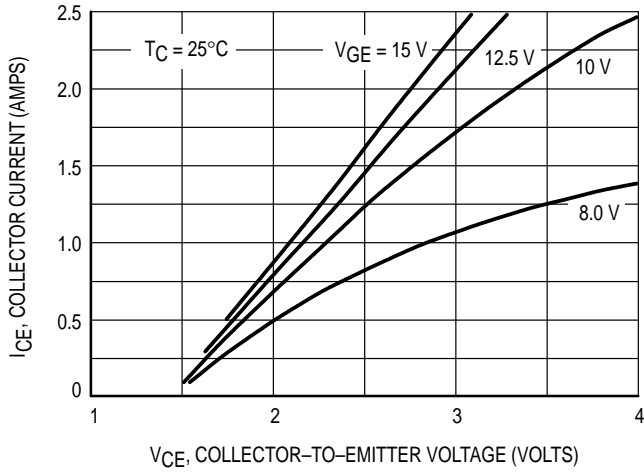


Figure 1. Saturation Characteristics

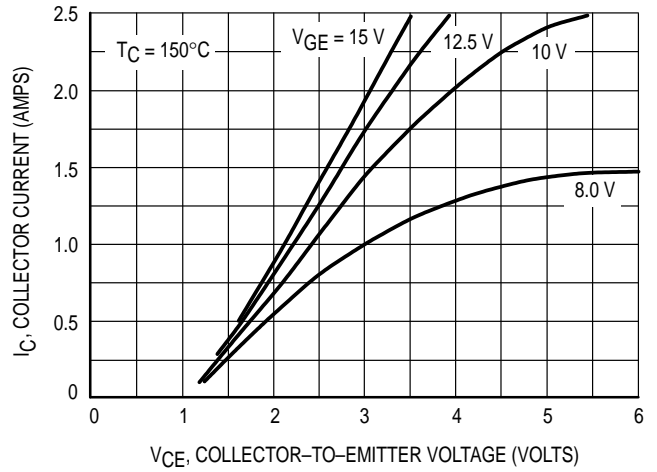


Figure 2. Saturation Characteristics

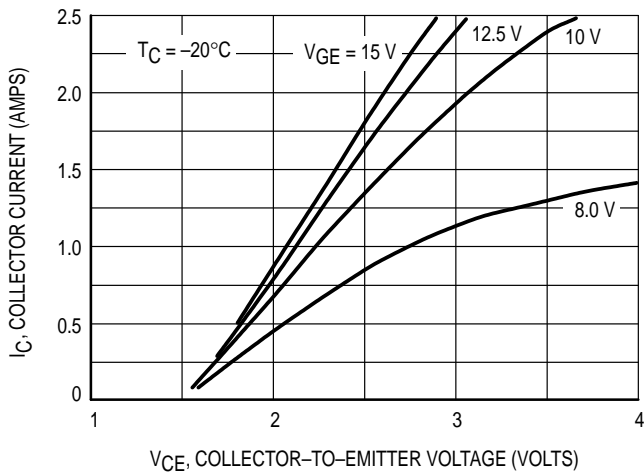


Figure 3. Saturation Characteristics

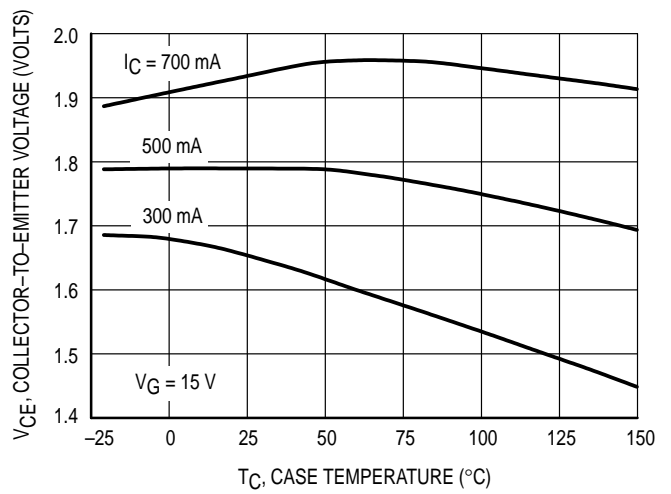


Figure 4. Collector-To-Emitter Saturation Voltage versus Case Temperature

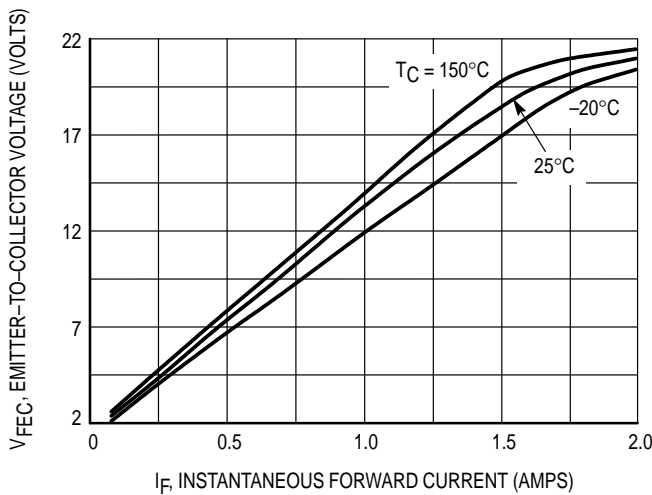


Figure 5. Diode Forward Voltage Drop

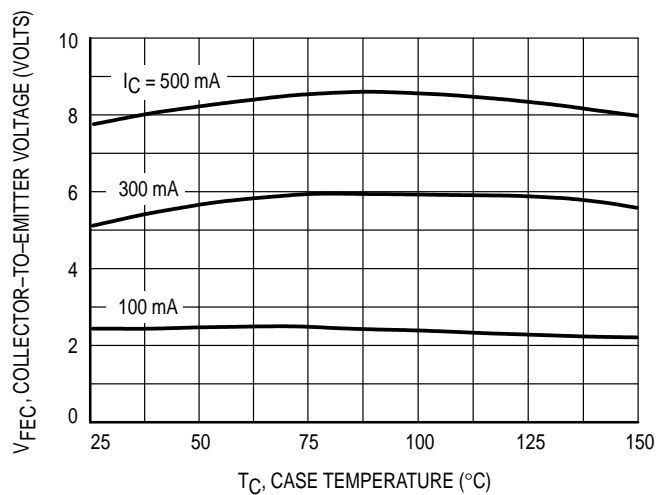


Figure 6. Diode Forward Voltage versus Case Temperature

MGS05N60D

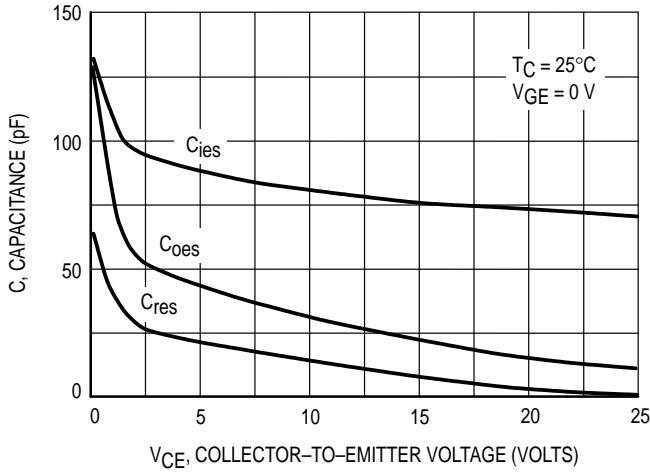


Figure 7. Capacitance Variation

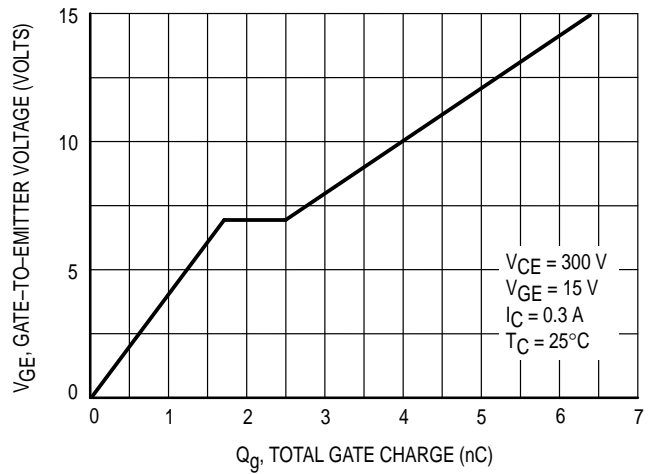


Figure 8. Gate-To-Emitter Voltage versus Total Charge

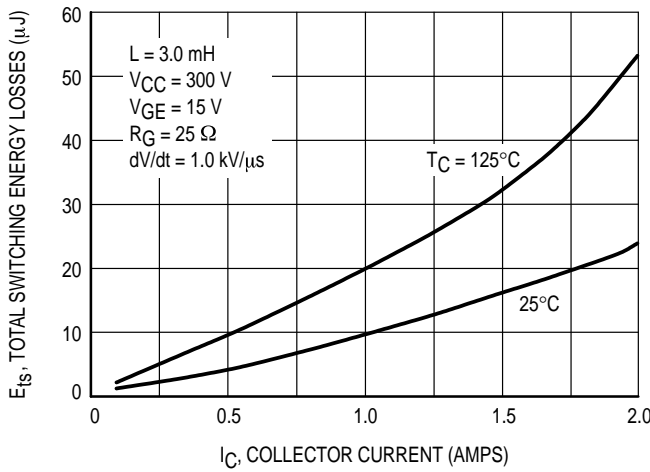


Figure 9. Total Switching Losses versus Collector Current

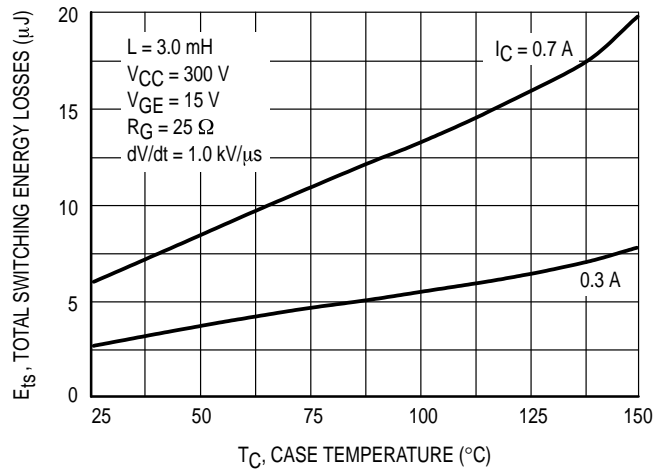


Figure 10. Total Switching Losses versus Case Temperature

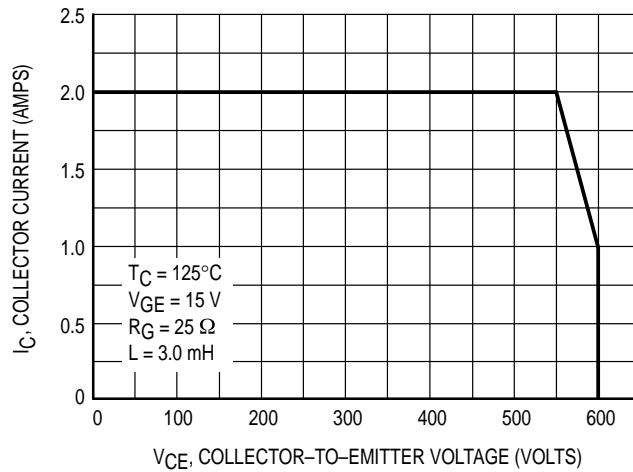


Figure 11. Minimum Turn-Off Safe Operating Area

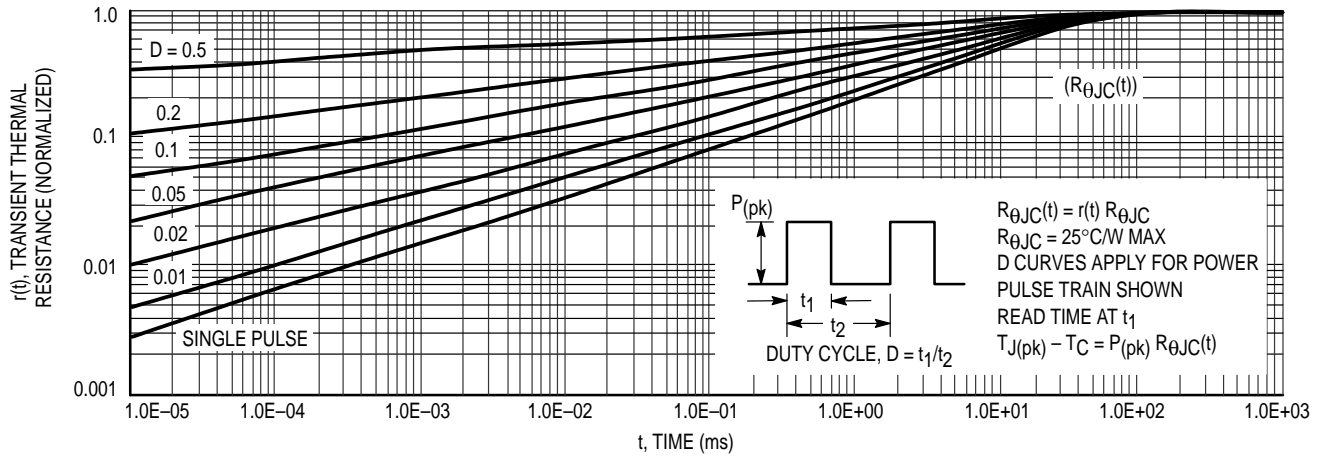
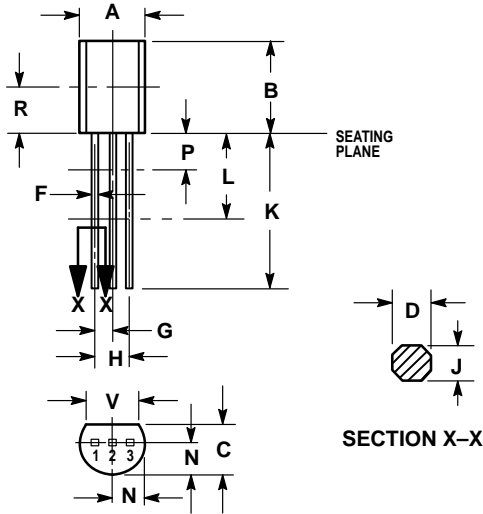


Figure 12. Typical Thermal Response

PACKAGE DIMENSIONS



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSIONS D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.022	0.46	0.56
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500	—	12.70	—
L	0.250	—	6.35	—
N	0.080	0.105	2.04	2.66
P	—	0.100	—	2.54
R	0.135	—	3.43	—
V	0.135	—	3.43	—

- STYLE 35:
- PIN 1. GATE
 - COLLECTOR
 - EMITTER

CASE 029-05
TO-226AE
ISSUE AD

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